

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A method for forming photoresist pattern for use in manufacture of semiconductor device, including a step of forming a porous underlayer coating on a semiconductor substrate; a step of forming a photoresist layer on the porous underlayer coating; a step of exposing the semiconductor substrate covered with the porous underlayer coating and the photoresist to light; a step of developing the photoresist after the exposure to light; and a step of removing the porous underlayer coating corresponding to a part of developed and removed photoresist by etching.
2. (Original) The method for forming photoresist pattern according to claim 1, further including a step of forming an anti-reflective coating or a flattening coating before or after the step of forming a porous underlayer coating on a semiconductor substrate.
3. (Original) The method for forming photoresist pattern according to claim 1, wherein the porous underlayer coating is formed by applying an underlayer coating forming composition containing a blowing agent or a polymer having a blowing group on a semiconductor substrate, and heating it.
4. (Original) An underlayer coating forming composition for forming a porous underlayer coating for use in manufacture of semiconductor device, comprising a blowing agent, an organic material and a solvent.

5. (Original) An underlayer coating forming composition for forming a porous underlayer coating for use in manufacture of semiconductor device, comprising a polymer having a blowing group and a solvent.
6. (Original) An underlayer coating forming composition for forming a porous underlayer coating for use in manufacture of semiconductor device, comprising a polymer having a blowing group, an organic material and a solvent.
7. (Original) The underlayer coating forming composition according to claim 4, wherein the blowing agent is a blowing agent that is decomposed with heat to generate nitrogen, carbon dioxide or water vapor.
8. (Currently Amended) The underlayer coating forming composition according to claim 5 ~~or~~ 6, wherein the polymer having a blowing group is a polymer that is decomposed with heat to generate nitrogen, carbon dioxide or water vapor.
9. (Currently Amended) The underlayer coating forming composition according to claim 4 ~~or~~ 6, wherein the organic material is an organic material containing at least one component selected from the group consisting of a polymer, a crosslinking compound and a light absorbing compound.
10. (Original) The underlayer coating forming composition according to claim 9, wherein the polymer is a polymer having at least one aromatic ring structure selected from the group consisting of a benzene ring, a naphthalene ring, an anthracene ring and a triazine ring.

11. (Original) The underlayer coating forming composition according to claim 9, wherein the crosslinking compound is a compound having at least two crosslink forming substituents.

12. (Original) The underlayer coating forming composition according to claim 9, wherein the light absorbing compound is a compound having at least one ring structure selected from the group consisting of a benzene ring, a naphthalene ring, an anthracene ring and a triazine trione ring.

13. (Currently Amended) A method for forming photoresist pattern for use in manufacture of semiconductor device, including a step of forming a porous underlayer coating by applying the underlayer coating forming composition according to claim 4 ~~any one of claims 4 to 12~~ on a semiconductor substrate and heating it; a step of forming a photoresist layer on the porous underlayer coating; a step of exposing the semiconductor substrate covered with the porous underlayer coating and the photoresist to light; a step of developing the photoresist after the exposure to light; and a step of removing the porous underlayer coating corresponding to a part of developed and removed photoresist by etching.